



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	5.0Ω @ V _{GS} = 10V	210mA
60V	7.5Ω @ V _{GS} = 5V	170mA

Description

This MOSFET is designed to minimize the on-state resistance $(R_{\text{DS(ON)}})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features

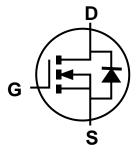
- Low On-Resistance: R_{DS(ON)}
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

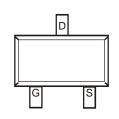
- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 🔞
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)







Equivalent Circuit



Top View
Pin Out Configuration

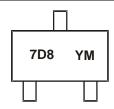
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN67D8LT-7	SOT523	3000/Tape & Reel
DMN67D8LT-13	SOT523	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



7D8 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014)

M = Month (ex: 9 = September)

Date Code Key

Date Code Rey												
Year	2014	2	2015	2016		2017	2018		2019	2020		2021
Code	В		С	D		E	F		G	Н		ı
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	60	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I _D	210 170	mA
Maximum Continuous Body Diode Forward Curren	t (Note 6)	I _S	0.5	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	0.8	Α	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

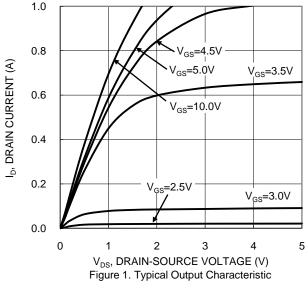
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	260	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	497	°C/W
Total Power Dissipation (Note 6)		P _D	350	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	366	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

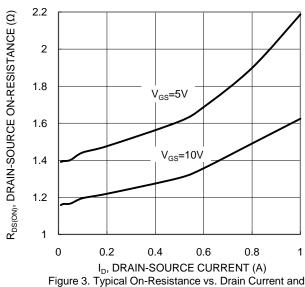
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

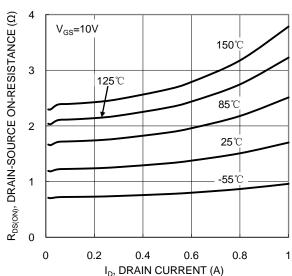
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Pages		3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		1.5	5.0	52	$V_{GS} = 10V, I_D = 0.5A$	
Forward Transconductance	g FS	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage	V_{SD}		0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	22	_	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	4.1	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	2.5	_	pF	1 = 1.001112	
Gate Resistance	R_g		120	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	361	_		V 40V I 050A	
Total Gate Charge (V _{GS} = 10V)	Q_g	_	821	_	рС		
Gate-Source Charge	Q_{gs}	_	162	_	рС	$V_{DS} = 10V, I_{D} = 250mA$	
Gate-Drain Charge	Q_{gd}	_	116	_			
Turn-On Delay Time	t _{D(ON)}	_	2.8	_		V 00V I 0.04	
Turn-On Rise Time	t _R	_	3.0	_	nc	$V_{DD} = 30V, I_D = 0.2A,$	
Turn-Off Delay Time	t _{D(OFF)}	_	7.6	_	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$	
Turn-Off Fall Time	t _F	_	5.6	_		2022	

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



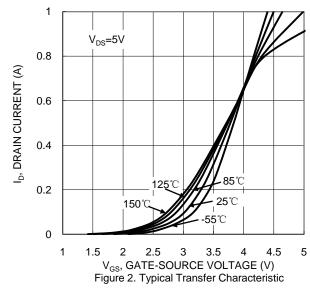


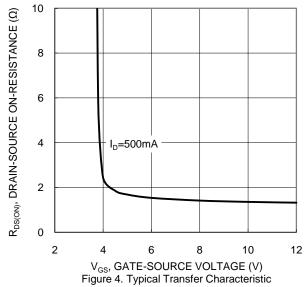




Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





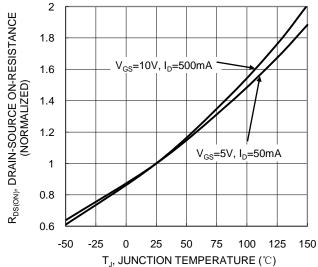


Figure 6. On-Resistance Variation with Junction Temperature



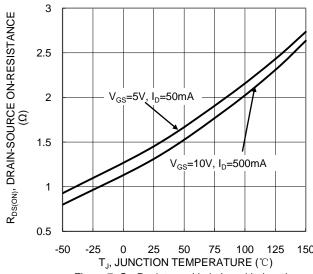
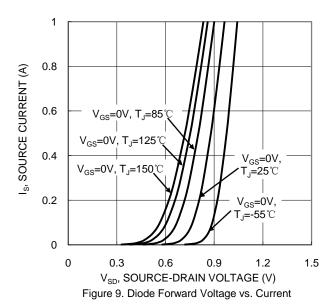
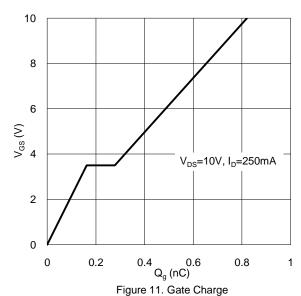


Figure 7. On-Resistance Variation with Junction Temperature





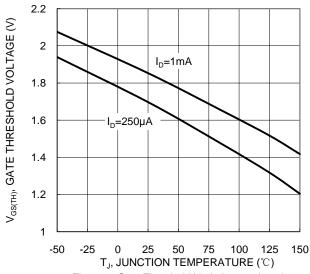
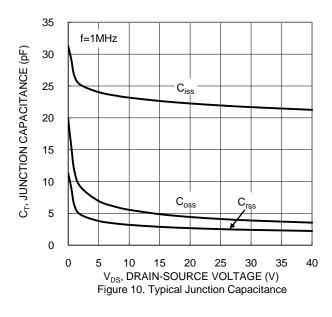
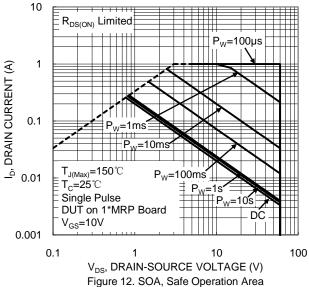


Figure 8. Gate Threshold Variation vs. Junction Temperature







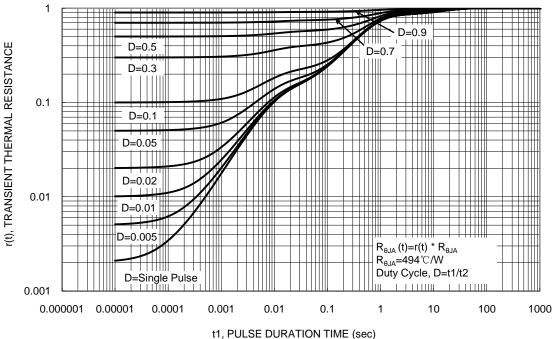
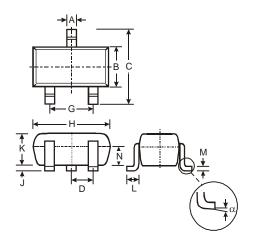


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT523



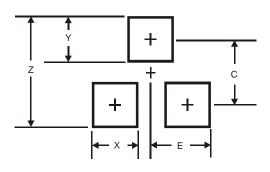
SOT523							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
С	1.45	1.75	1.60				
D			0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
J	0.00	0.10	0.05				
K	0.60	0.80	0.75				
L	0.10	0.30	0.22				
M	0.10	0.20	0.12				
N	0.45	0.65	0.50				
α	0°	8°					
All Dimensions in mm							



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT523



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
E	0.7

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